1-of-8 Decoder/ Demultiplexer

High-Performance Silicon-Gate CMOS

The MC74HC238A is identical in pinout to the LS238. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

The HC238A decodes a three-bit Address to one-of-eight active-high outputs. This device features three Chip Select inputs, two active-low and one active-high to facilitate the demultiplexing, cascading, and chip-selecting functions. The demultiplexing function is accomplished by using the Address inputs to select the desired device output; one of the Chip Selects is used as a data input while the other Chip Selects are held in their active states.

Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2.0 V to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 100 FETs or 29 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These are Pb-Free Devices*



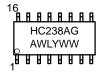
ON Semiconductor®

www.onsemi.com

MARKING DIAGRAMS



SOIC-16 D SUFFIX CASE 751B





TSSOP-16 DT SUFFIX CASE 948F



= Assembly Location

WL, L = Wafer Lot Y = Year WW, W = Work Week G or = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

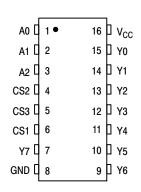


Figure 1. Pin Assignment

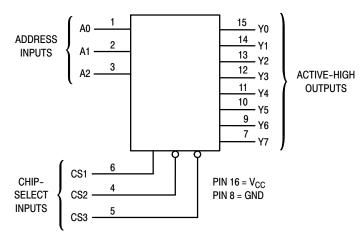


Figure 2. Logic Diagram

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HC238ADG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74HC238ADR2G	SOIC-16	2500 Tape & Reel
NLV74HC238ADR2G*	(Pb-Free)	
MC74HC238ADTG	TSSOP-16 (Pb-Free)	96 Units / Tube
MC74HC238ADTR2G	TSSOP-16	2500 Tape & Reel
NLV74HC238ADTR2G*	(Pb-Free)	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TRUTH TABLE

		Inp	uts			Outputs							
CS3	CS2	CS1	A0	A 1	A2	Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y7
Н	Х	Х	Х	Х	Х	L	L	L	L	L	L	L	L
Х	Н	Х	Х	Х	Х	L	L	L	L	L	L	L	L
Х	Х	L	Χ	Х	Х	L	L	L	L	L	L	L	L
L	L	Н	L	L	L	Н	L	L	L	L	L	L	L
L	L	Н	Н	L	L	L	Н	L	L	L	L	L	L
L	L	Н	L	Н	L	L	L	Н	L	L	L	L	L
L	L	Н	Н	Н	L	L	L	L	Н	L	L	L	L
L	L	Н	L	L	Н	L	L	L	L	Н	L	L	L
L	L	Н	Н	L	Н	L	L	L	L	L	Н	L	L
L	L	Н	L	Н	Н	L	L	L	L	L	L	Н	L
L	L	Н	Н	Н	Н	L	L	L	L	L	L	L	Н

^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
l _{in}	DC Input Current, per Pin	± 20	mA
l _{out}	DC Output Current, per Pin	± 25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	± 50	mA
P _D	Power Dissipation in Still Air, SOIC Package† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (SOIC or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating – SOIC Package: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 .W/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V	
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to G	0	V _{CC}	V	
T _A	Operating Temperature, All Package Types		- 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time $V_{CC} = 2$ (Figure 2) $V_{CC} = 4$ $V_{CC} = 6$.5 V	0 0 0	1000 500 400	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Guara			
Symbol	Parameter	Test Conditions	v _{cc}	-55°C to 25°C	≤ 85 ° C	≤ 125°C	Unit
V _{IH}	Minimum High-Level Input	V _{out} = 0.1 V or V _{CC} - 0.1 V	2.0	1.5	1.5	1.5	V
	Voltage	$ I_{out} \leq 20 \mu A$	3.0	2.1	2.1	2.1	
			4.5	3.15	3.15	3.15	
			6.0	4.2	4.2	4.2	
V _{IL}	Maximum Low-Level Input	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$	2.0	0.5	0.5	0.5	V
	Voltage	$ I_{out} \leq 20 \mu A$	3.0	0.9	0.9	0.9	
			4.5	1.35	1.35	1.35	
			6.0	1.8	1.8	1.8	
V _{OH}	Minimum High-Level Output	$V_{in} = V_{IH}$ or V_{IL}	2.0	1.9	1.9	1.9	V
	Voltage	$ I_{out} \leq 20 \mu A$	4.5	4.4	4.4	4.4	
			6.0	5.9	5.9	5.9	
		$V_{in} = V_{IH} \text{ or } V_{IL} I_{out} \le 2.4 \text{ mA}$	3.0	2.48	2.34	2.20	
		$ I_{out} \le 4.0 \text{ mA}$	4.5	3.98	3.84	3.70	
		$ I_{out} \le 5.2 \text{ mA}$	6.0	5.48	5.34	5.20	
V _{OL}	Maximum Low-Level Output	$V_{in} = V_{IH}$ or V_{IL}	2.0	0.1	0.1	0.1	V
-	Voltage	$ I_{out} \leq 20 \mu A$	4.5	0.1	0.1	0.1	
			6.0	0.1	0.1	0.1	

V _{OL}	Maximum Low–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu A$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$\begin{split} V_{in} = V_{IH} \text{ or } V_{IL} & I_{out} \leq 2.4 \text{ mA} \\ & I_{out} \leq 4.0 \text{ mA} \\ & I_{out} \leq 5.2 \text{ mA} \end{split}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
I _{in}	Maximum Input Leakage Current	$V_{in} = V_{CC}$ or GND	6.0	± 0.1	± 1.0	± 1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	4	40	160	μΑ

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6.0 \text{ ns}$)

		V _{CC}	Guara	nteed Limit		
Symbol	Parameter	v	-55°C to 25°C	≤ 85°C	≤ 125°C	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A to Output Y (Figures 3 and 6)	2.0 3.0 4.5 6.0	135 90 27 23	170 125 34 29	205 165 41 35	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, CS1 to Output Y (Figures 4 and 6)	2.0 3.0 4.5 6.0	110 85 22 19	140 100 28 24	165 125 33 28	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, CS2 or CS3 to Output Y (Figures 5 and 6)	2.0 3.0 4.5 6.0	120 90 24 20	150 120 30 26	180 150 36 31	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 4 and 6)	2.0 3.0 4.5 6.0	75 30 15 13	95 40 19 16	110 55 22 19	ns
C _{in}	Maximum Input Capacitance	_	10	10	10	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Per Package)*	55	pF

^{*}Used to determine the no–load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

SWITCHING WAVEFORMS

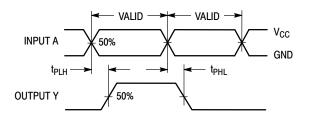


Figure 3.

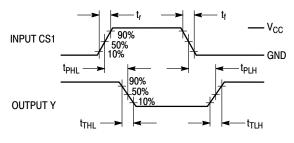


Figure 4.

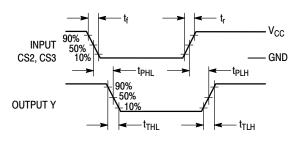
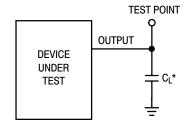


Figure 5.



*Includes all probe and jig capacitance

Figure 6. Test Circuit

PIN DESCRIPTIONS

ADDRESS INPUTS A0, A1, A2 (Pins 1, 2, 3)

Address inputs. These inputs, when the chip is selected, determine which of the eight outputs is active—low.

CONTROL INPUTS CS1, CS2, CS3 (Pins 6, 4, 5)

Chip select inputs. For CS1 at a high level and CS2, CS3 at a low level, the chip is selected and the outputs follow the

Address inputs. For any other combination of CS1, CS2, and CS3, the outputs are at a logic low.

OUTPUTS

Y0 - Y7 (Pins 15, 14, 13, 12, 11, 10, 9, 7)

Active-high Decoded outputs. These outputs assume a high level when addressed and the chip is selected. These outputs remain low when not addressed or the chip is not selected.

EXPANDED LOGIC DIAGRAM

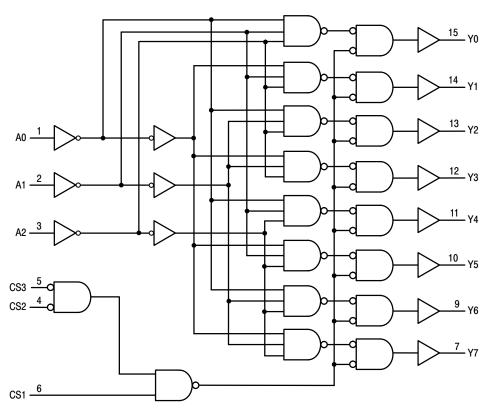
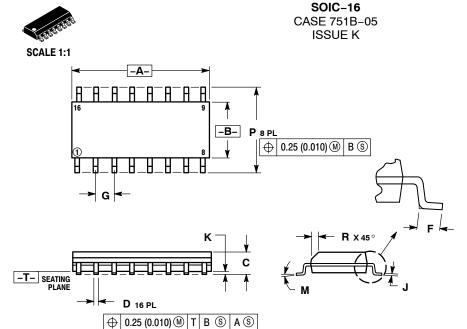


Figure 7. Logic Diagram

MECHANICAL CASE OUTLINE



DATE 29 DEC 2006

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

 SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
Р	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

2. 3.	COLLECTOR BASE EMITTER NO CONNECTION EMITTER BASE COLLECTOR COLLECTOR BASE EMITTER NO CONNECTION EMITTER BASE	2. 3. 4. 5. 6. 7. 8. 9. 10.	CATHODE ANODE NO CONNECTION CATHODE CATHODE NO CONNECTION ANODE CATHODE CATHODE ANODE NO CONNECTION CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE	2. 3. 4. 5. 6. 7. 8. 9. 10.	COLLECTOR, DYE #1 BASE, #1 EMITTER, #1 COLLECTOR, #1 COLLECTOR, #2 BASE, #2 EMITTER, #2 COLLECTOR, #2 COLLECTOR, #2 COLLECTOR, #3	STYLE 4: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	COLLECTOR, #1 COLLECTOR, #2 COLLECTOR, #3 COLLECTOR, #3 COLLECTOR, #4 COLLECTOR, #4 BASE, #4 EMITTER, #4 BASE, #3		
14.	COLLECTOR		NO CONNECTION	14.		14.		SOLDERING	FOOTPRINT
15.	EMITTER		ANODE	15.		15.		8)	(
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1	6.4	
STYLE 5: PIN 1. 2. 3. 4. 5. 6. 7. 8.	DRAIN, DYE #1 DRAIN, #1 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4	STYLE 6: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	CATHODE	STYLE 7: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	SOURCE N-CH COMMON DRAIN (OUTPU' GATE P-CH COMMON DRAIN (OUTPU' COMMON DRAIN (OUTPU' COMMON DRAIN (OUTPU' SOURCE P-CH SOURCE P-CH	T) T) T)	1 0.	6X 1 1 1 1 1 1 1 1 1 1	16
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPUT	T)			
11.	GATE, #3	11.		11.	COMMON DRAIN (OUTPUT				
12.	SOURCE, #3	12.	ANODE	12.	COMMON DRAIN (OUTPUT				1.07
13.	GATE, #2	13.	ANODE	13.	GATE N-CH				
14.	SOURCE, #2	14.		14.	COMMON DRAIN (OUTPUT				↓ PITCH
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPUT	T)			+
16.	SOURCE, #1	16.	ANODE	16.	SOURCE N-CH			8	9 + - + + + + + + + + + + + + + + + + +

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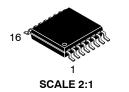
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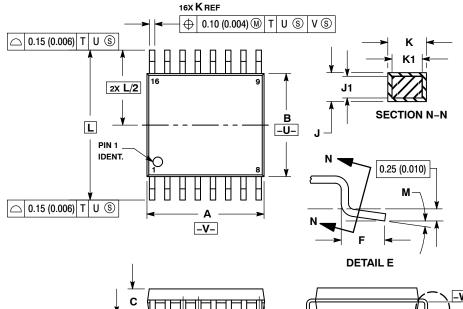
-T- SEATING PLANE





TSSOP-16 CASE 948F-01 ISSUE B

DATE 19 OCT 2006



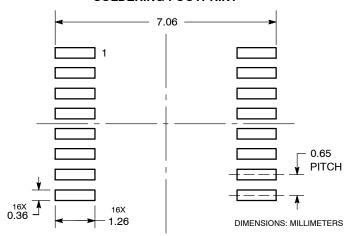
NOTES

- JIES:
 DIMENSIONING AND TOLERANCING PER
 ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD
 FLASH. PROTRUSIONS OR GATE BURRS.
 MOLD EL ROLL OF GATE BURDS SUAL NO.
- MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С	1.20			0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.18	0.28	0.007	0.011	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
Κ	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
Г	6.40 BSC		0.252	BSC	
М	0 °	8°	0 °	8 °	

SOLDERING FOOTPRINT

G



GENERIC MARKING DIAGRAM*

168888888 XXXX XXXX **ALYW** 188888888

XXXX = Specific Device Code Α = Assembly Location

= Wafer Lot L Υ = Year W = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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